


**VOIDLESS-HERMETICALLY-SEALED
STANDARD RECOVERY GLASS
RECTIFIERS**

 ALSO
AVAILABLE
IN
SURFACE
MOUNT

DESCRIPTION

This "standard recovery" rectifier diode series is military qualified to MIL-PRF-19500/427 and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 1.0 Amp rated rectifiers for working peak reverse voltages from 200 to 1000 volts are hermetically sealed with voidless-glass construction using an internal "Category I" metallurgical bond. These devices are also available in surface mount MELF package configurations by adding a "US" suffix (see separate data sheet for 1N5614US thru 1N5622US). Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including fast and ultrafast device types in both through-hole and surface mount packages.

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

FEATURES

- Popular JEDEC registered 1N5614 to 1N5622 series
- Voidless hermetically sealed glass package
- Triple-Layer Passivation
- Internal "Category I" Metallurgical bonds
- Working Peak Reverse Voltage 200 to 1000 Volts.
- JAN, JANTX, JANTXV, and JANS available per MIL-PRF-19500/427
- Surface mount equivalents also available in a square end-cap MELF configuration with "US" suffix (see separate data sheet for 1N5614US thru 1N5622US)

MAXIMUM RATINGS

- Junction & Storage Temperature: -65°C to $+200^{\circ}\text{C}$
- Thermal Resistance: 38°C/W junction to lead at 3/8 inch (10 mm) lead length from body
- Thermal Impedance: 4.5°C/W @ 10 ms heating time
- Average Rectified Forward Current (I_o): 1.0 Amps @ $T_A = 55^{\circ}\text{C}$ and 0.75 Amps @ $T_A = 100^{\circ}\text{C}$
- Forward Surge Current: 30 Amps @ 8.3 ms half-sine
- Solder Temperatures: 260°C for 10 s (maximum)

APPLICATIONS / BENEFITS

- Standard recovery 1 Amp rectifiers 200 to 1000 V
- Military and other high-reliability applications
- General rectifier applications including bridges, half-bridges, catch diodes, etc.
- High forward surge current capability
- Extremely robust construction
- Low thermal resistance
- Controlled avalanche with peak reverse power capability
- Inherently radiation hard as described in Microsemi MicroNote 050

MECHANICAL AND PACKAGING

- CASE: Hermetically sealed voidless hard glass with Tungsten slugs (package dimensions on last page)
- TERMINATIONS: Axial leads are copper with Tin/Lead (Sn/Pb) finish. Note: Previous JANS inventory had solid Silver axial-leads and no finish.
- MARKING: Body paint and part number, etc.
- POLARITY: Cathode band
- TAPE & REEL option: Standard per EIA-296
- WEIGHT: 340 mg

ELECTRICAL CHARACTERISTICS

| TYPE | WORKING PEAK REVERSE VOLTAGE V_{RWM} | MINIMUM BREAKDOWN VOLTAGE V_{BR} @ 50 μA | AVERAGE RECTIFIED CURRENT I_o @ T_A (NOTE 1) | FORWARD VOLTAGE (MAX.) V_F @ 3A | REVERSE CURRENT (MAX.) I_R @ V_{RWM} | MAXIMUM SURGE CURRENT I_{FSM} (NOTE 2) | REVERSE RECOVERY (NOTE 3) t_{rr} |
|--------|---|--|--|--|---|--|---|
| | | | | | | | |
| | | | | 55°C | 100°C | | |
| 1N5614 | 200 | 220 | 1.00 | .750 | | 0.5 | 25 |
| 1N5616 | 400 | 440 | 1.00 | .750 | 0.8 MIN. | 0.5 | 25 |
| 1N5618 | 600 | 660 | 1.00 | .750 | | 0.5 | 25 |
| 1N5620 | 800 | 880 | 1.00 | .750 | 1.3 MAX. | 0.5 | 25 |
| 1N5622 | 1000 | 1100 | 1.00 | .750 | | 0.5 | 25 |

NOTE 1: From 1 Amp at $T_A = 55^{\circ}\text{C}$, derate linearly at 5.56 mA/ $^{\circ}\text{C}$ to 0.75 Amp at $T_A = 100^{\circ}\text{C}$. From $T_A = 100^{\circ}\text{C}$, derate linearly at 7.5 mA/ $^{\circ}\text{C}$ to 0 Amps at $T_A = 200^{\circ}\text{C}$. These ambient ratings are for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where $T_{J(max)}$ does not exceed 175 °C.

NOTE 2: $T_A = 100^{\circ}\text{C}$, $f = 60$ Hz, $I_o = 750$ mA for ten 8.3 ms surges @ 1 minute intervals

NOTE 3: $I_F = 0.5\text{A}$, $I_{RM} = 1\text{A}$, $I_{R(REC)} = 0.250\text{A}$

**Microsemi**

SCOTTSDALE DIVISION

1N5614 thru 1N5622**RECTIFIERS****www. Microsemi .com****1N5614 – 1N5622****SYMBOLS & DEFINITIONS**

| Symbol | Definition |
|-----------|---|
| V_{BR} | Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current |
| V_{RWM} | Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range |
| I_o | Average Rectified Output Current: Output Current averaged over a full cycle with a 50 hZ or 60 Hz sine-wave input and a 180 degree conduction angle |
| V_F | Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current |
| I_R | Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature |
| C | Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage |
| t_{rr} | Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs. |

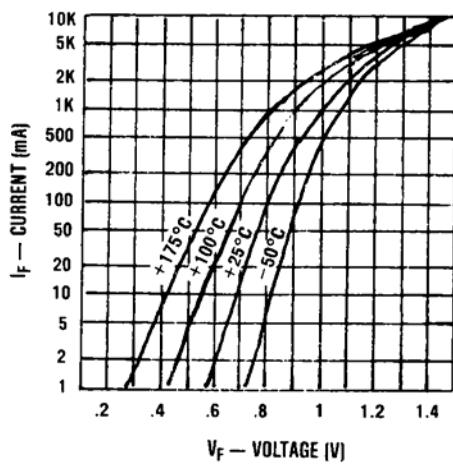
GRAPHS

FIGURE 1
TYPICAL FORWARD VOLTAGE vs FORWARD CURRENT

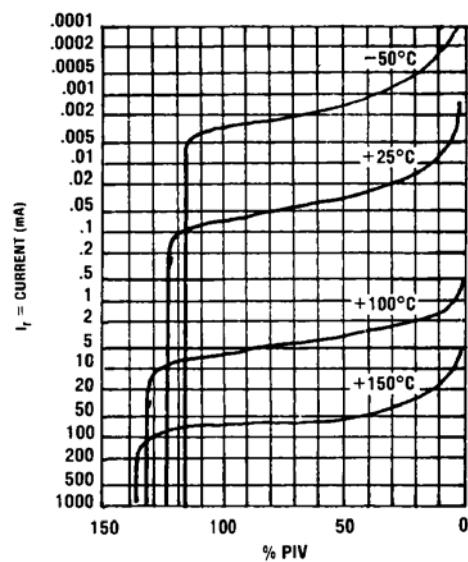


FIGURE 2
TYPICAL REVERSE CURRENT vs PIV



Microsemi

SCOTTSDALE DIVISION

1N5614 thru 1N5622

RECTIFIERS

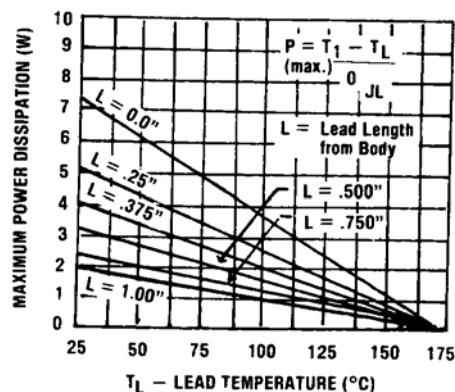


FIGURE 3
MAXIMUM POWER DISSIPATION
vs LEAD TEMPERATURE

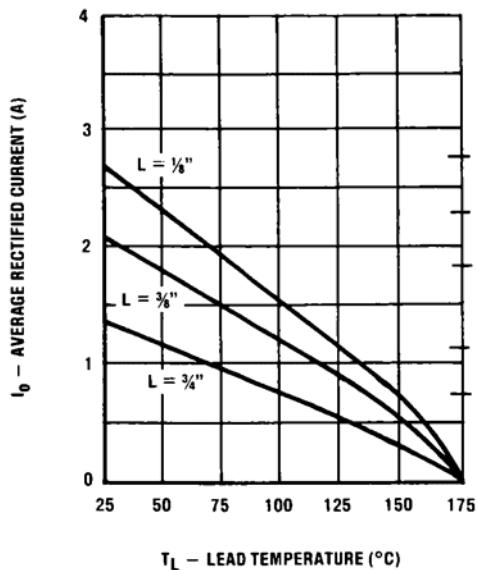
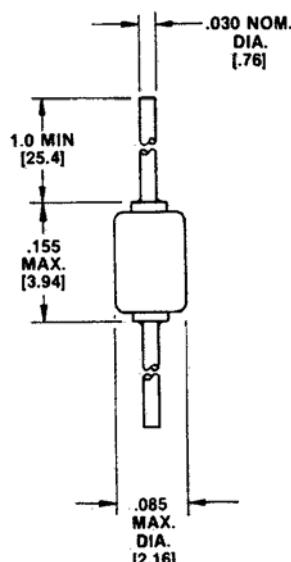


FIGURE 4
MAXIMUM CURRENT vs LEAD TEMPERATURE

PACKAGE DIMENSIONS



Dimensions: Inches/mm
NOTE: Lead tolerance = +0.003/-0.004 inches